

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (original): A pn. junction type Group III nitride semiconductor light-emitting device having a light-emitting layer of multiple quantum well structure in which well layers and barrier layers including Group III nitride semiconductors are alternately stacked periodically between an n-type clad layer and a p-type clad layer which are formed on a crystal substrate and which include Group III nitride semiconductors,

wherein one end layer of the light-emitting layer is closest to and opposed to the n-type clad layer, and the other end layer of the light-emitting layer is closest to and opposed to the p-type clad layer, both the one and the other end layers are barrier layers, and the other end layer is thicker than the barrier layer of the one end layer.

2. (original): The pn junction type Group III nitride semiconductor light-emitting device according to claim 1, wherein each of the barrier layers has a thickness increased gradually from the one end layer toward the other end layer.

3. (currently amended): The pn junction type GROUP III nitride semiconductor light-emitting device according to claim 1-~~or~~2, wherein the other end layer has an impurity concentration low

Preliminary Amendment

Appln. No.: National Stage of PCT/JP2005/004390

at its junction portion relative to the well layer, highest at its central portion and reduced gradually from the central portion toward the p- type clad layer.

4. (currently amended): The pn junction type GROUP III nitride semiconductor light-emitting device according to claim 1~~any one of claims 1 to 3~~, wherein the other end layer has joined thereto a well layer which. is not intentionally doped with impurities.